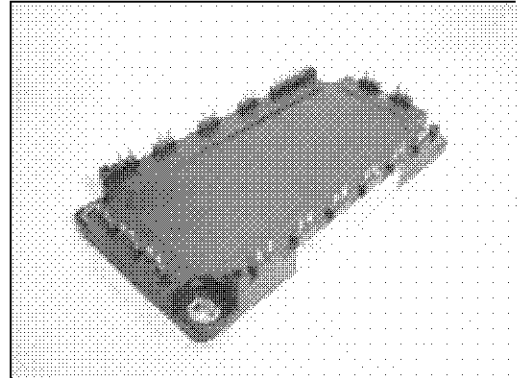


IGBT MODULE (S series) 1200V / 50A / PIM



■ Features

- Low $V_{CE(sat)}$
- Compact package
- P.C. board mount
- Converter diode bridge, Dynamic brake circuit

■ Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

■ Maximum ratings and characteristics

● Absolute maximum ratings ($T_c=25^\circ\text{C}$ unless without specified)

Item		Symbol	Condition		Rating	Unit
Inverter	Collector-Emitter voltage	V_{CES}			1200	V
	Gate-Emitter voltage	V_{GES}			± 20	V
	Collector current	I_C	Continuous	$T_c=25^{\circ}\text{C}$	75	A
				$T_c=80^{\circ}\text{C}$	50	
		I_{CP}	1ms	$T_c=25^{\circ}\text{C}$	150	A
				$T_c=80^{\circ}\text{C}$	100	
	$-I_C$			50	A	
Collector power dissipation		P_C	1 device		360	W
Brake	Collector-Emitter voltage	V_{CES}			1200	V
	Gate-Emitter voltage	V_{GES}			± 20	V
	Collector current	I_C	Continuous	$T_c=25^{\circ}\text{C}$	35	A
				$T_c=80^{\circ}\text{C}$	25	
		I_{CP}	1ms	$T_c=25^{\circ}\text{C}$	70	A
				$T_c=80^{\circ}\text{C}$	50	
Collector power dissipation		P_C	1 device		180	W
Repetitive peak reverse voltage		V_{RRM}			1200	V
Converter	Repetitive peak reverse voltage	V_{RRM}			1600	V
	Average output current	I_O	50Hz/60Hz sine wave		50	A
	Surge current (Non-Repetitive)	I_{FSM}	$T_J=150^{\circ}\text{C}$, 10ms		520	A
	I^2t (Non-Repetitive)	I^2t	half sine wave		1352	A^2s
Operating junction temperature		T_J			+150	$^{\circ}\text{C}$
Storage temperature		T_{stg}			-40 to +125	$^{\circ}\text{C}$
Isolation voltage	between terminal and copper base *2	V_{iso}	AC : 1 minute		AC 2500	V
	between thermistor and others *3				AC 2500	
Mounting screw torque					3.5 *1	N·m

*1 Recommendable value : 2.5 to 3.5 N·m (M5)

*2 All terminals should be connected together when isolation test will be done.

*3 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

● Electrical characteristics (T_j=25°C unless otherwise specified)

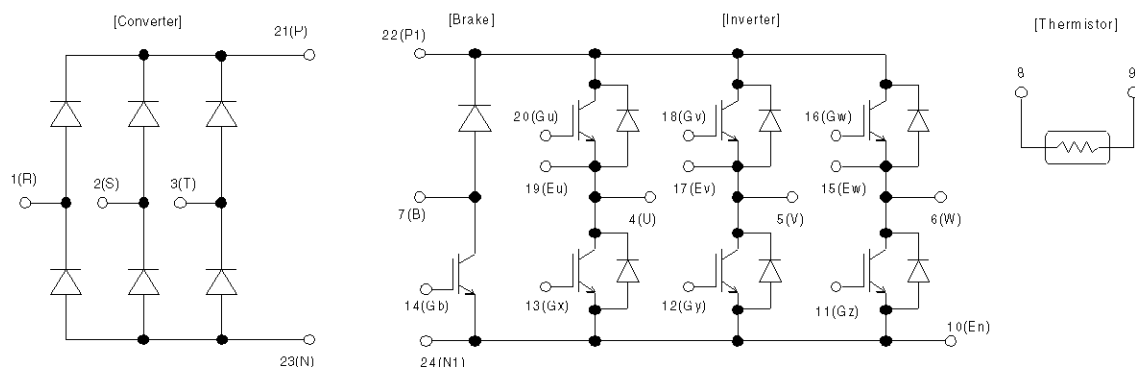
Item		Symbol	Condition	Characteristics			Unit
				Min.	Typ.	Max.	
Inverter	Zero gate voltage collector current	I _{CES}	V _{CE} =1200V, V _{GE} =0V			1.0	mA
	Gate-Emitter leakage current	I _{GES}	V _{CE} =0V, V _{GE} =±20V			0.2	μA
	Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} =20V, I _C =50mA	5.5	7.2	8.5	V
	Collector-Emitter saturation voltage	V _{CE(sat)}	V _{GE} =15V, I _C =50A	chip	2.1		V
			terminal		2.3	2.7	
	Input capacitance	C _{ies}	V _{GE} =0V, V _{CE} =10V, f=1MHz		6000		pF
	Turn-on time	t _{on}	V _{CC} =600V I _C =50A V _{GE} =±15V R _G =24Ω		0.35	1.2	μs
		t _r			0.25	0.6	
		t _{r(i)}			0.1		
	Turn-off time	t _{off}			0.45	1.0	
		t _i			0.08	0.3	
Brake	Forward on voltage	V _F	I _F =50A	chip	2.3		V
	Reverse recovery time of FRD	t _{rr}	I _F =50A	terminal	2.5	3.3	
							μs
	Zero gate voltage collector current	I _{CES}	V _{CE} =1200V, V _{GE} =0V			1.0	mA
	Gate-Emitter leakage current	I _{GES}	V _{CE} =0V, V _{GE} =±20V			0.2	μA
	Collector-Emitter saturation voltage	V _{CE(sat)}	I _C =25A, V _{GE} =15V	chip	2.1		V
			terminal		2.25	2.7	
	Turn-on time	t _{on}	V _{CC} =600V I _C =25A V _{GE} =±15V R _G =51Ω		0.35	1.2	μs
		t _r			0.25	0.6	
	Turn-off time	t _{off}			0.45	1.0	
		t _i			0.08	0.3	
Converter	Reverse current	I _{RRM}	V _R =1200V			1.0	mA
	Forward on voltage	V _{FM}	I _F =50A	chip	1.1		V
				terminal	1.2	1.5	
	Reverse current	I _{RRM}	V _R =1600V			1.0	mA
Thermistor	Resistance	R	T=25°C		5000		Ω
			T=100°C	465	495	520	
	B value	B	T=25/50°C	3305	3375	3450	K

● Thermal resistance Characteristics

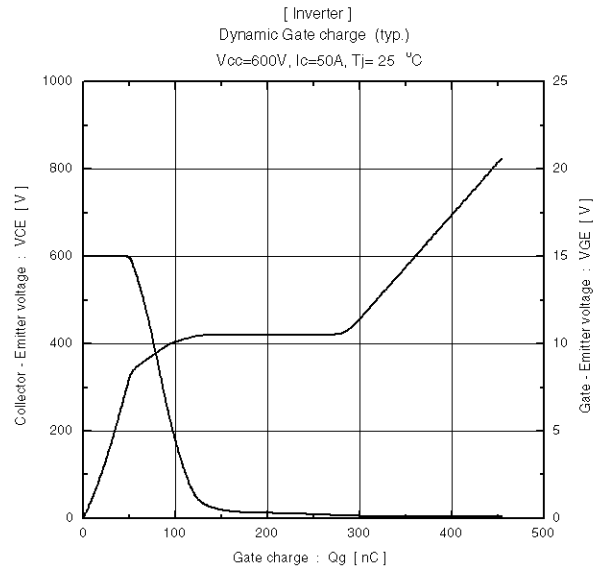
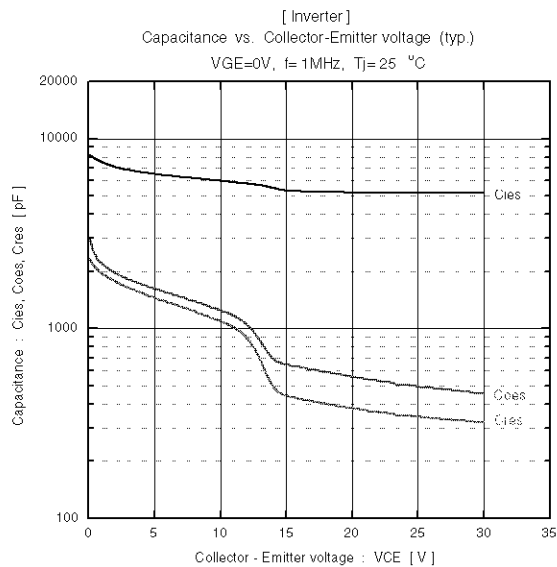
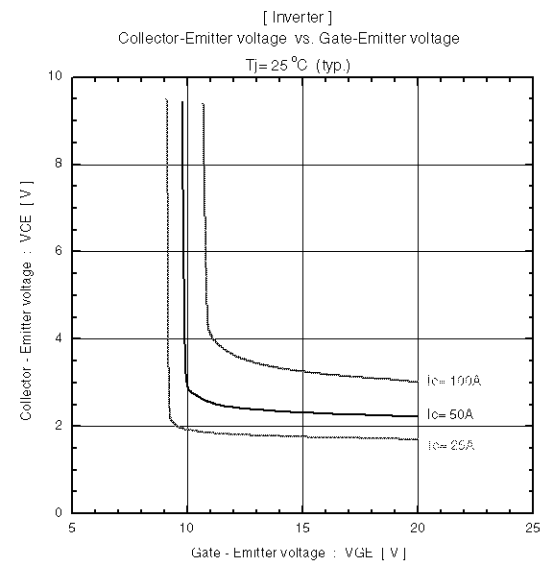
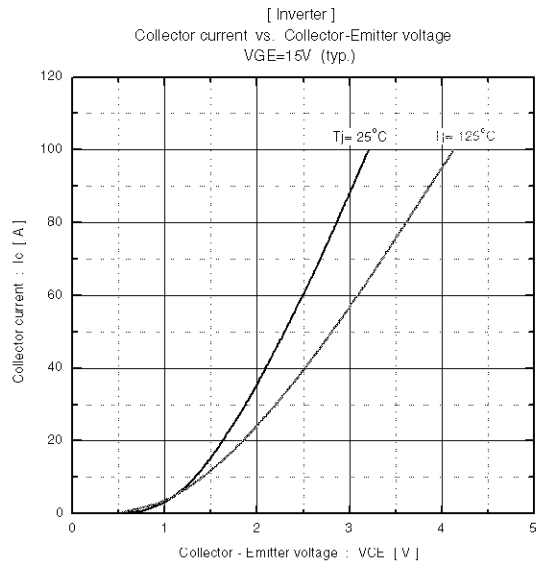
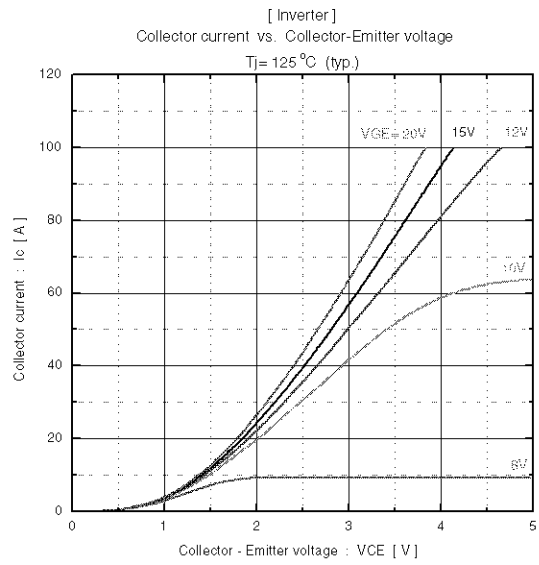
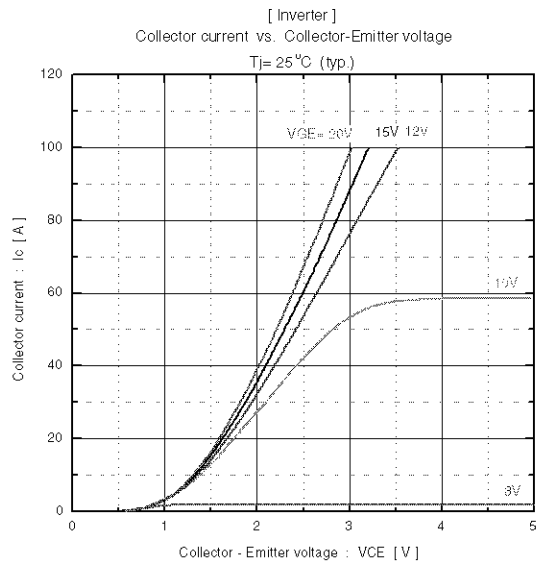
Item	Symbol	Condition	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance (1 device)	R _{th(j-c)}	Inverter IGBT			0.35	°C/W
		Inverter FWD			0.75	
		Brake IGBT			0.69	
		Converter Diode			0.50	
Contact thermal resistance *	R _{th(c-f)}	With thermal compound		0.05		

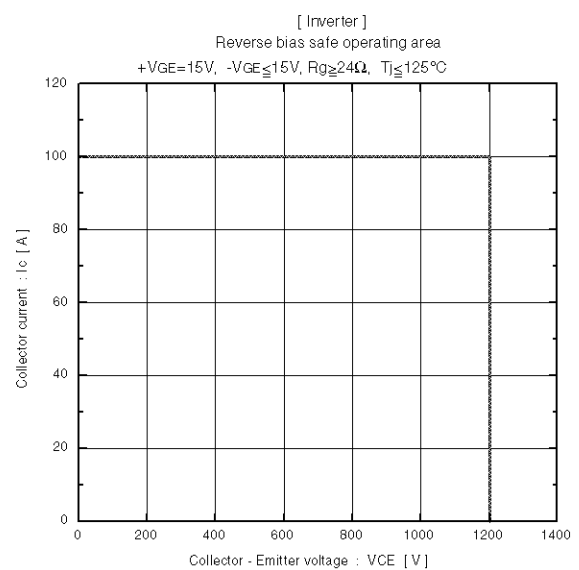
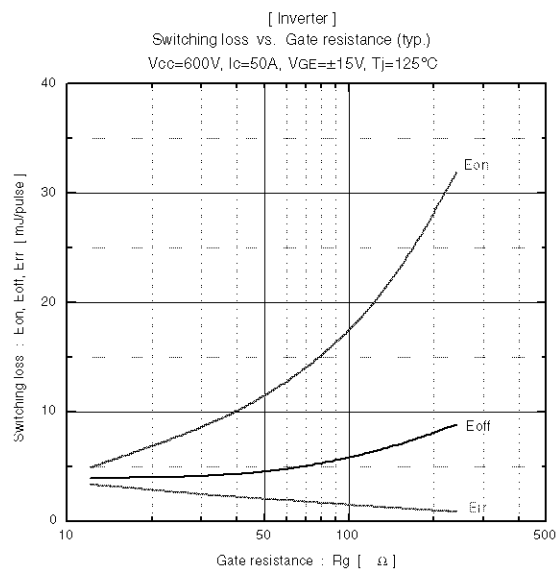
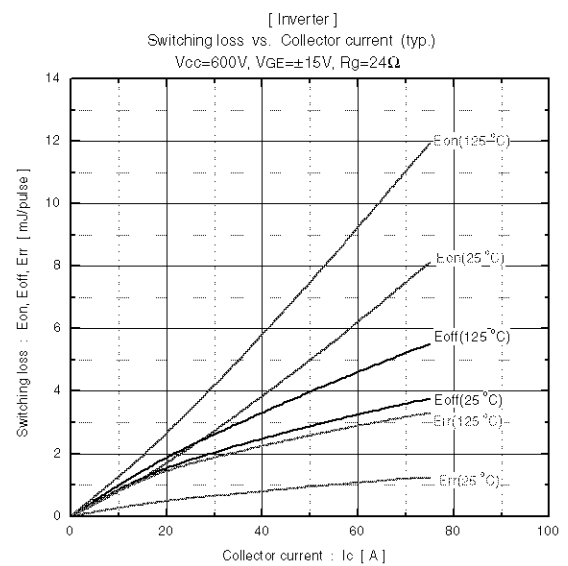
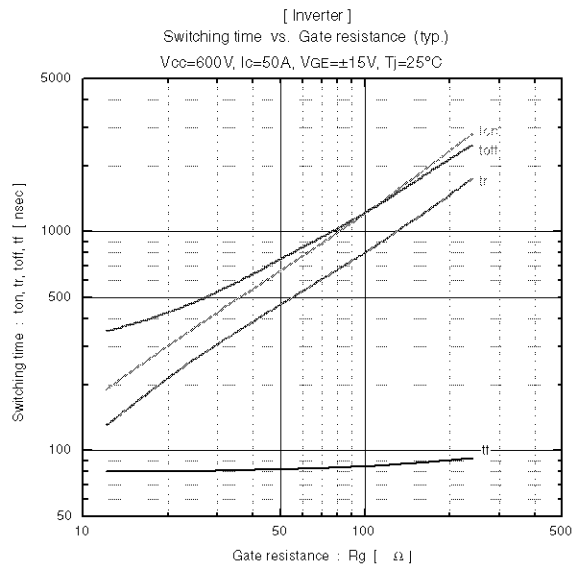
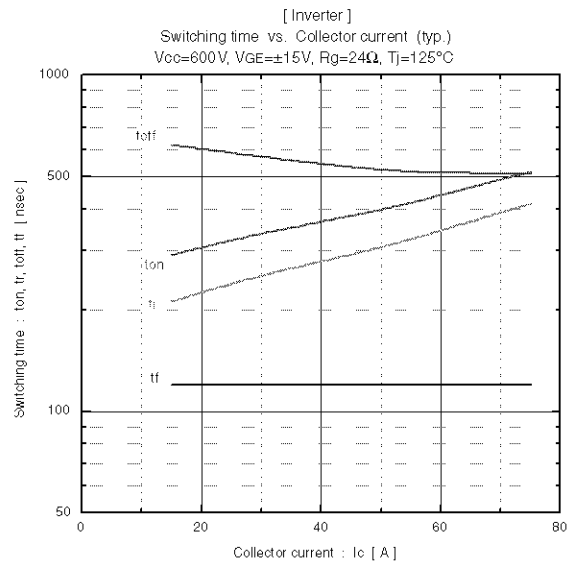
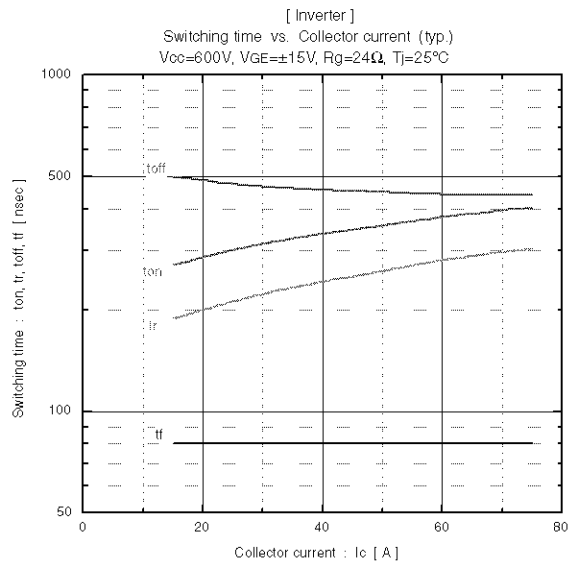
* This is the value which is defined mounting on the additional cooling fin with thermal compound

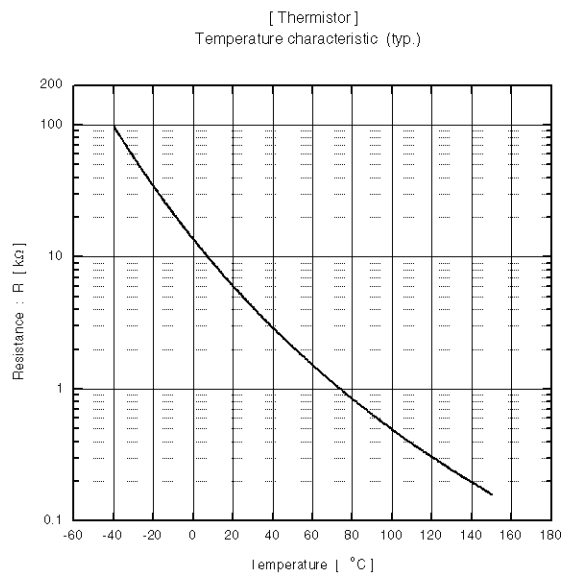
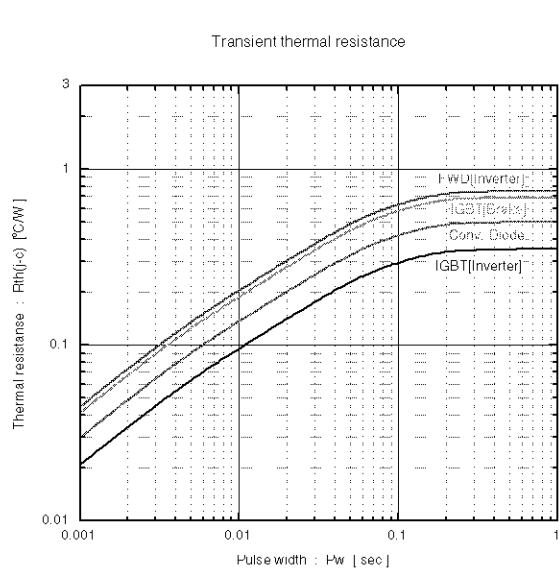
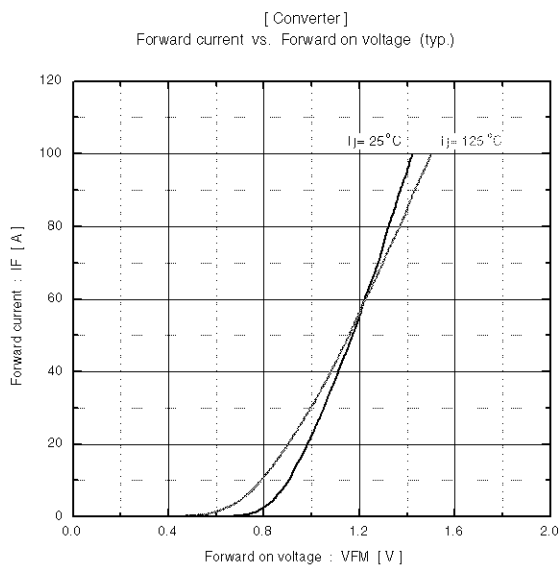
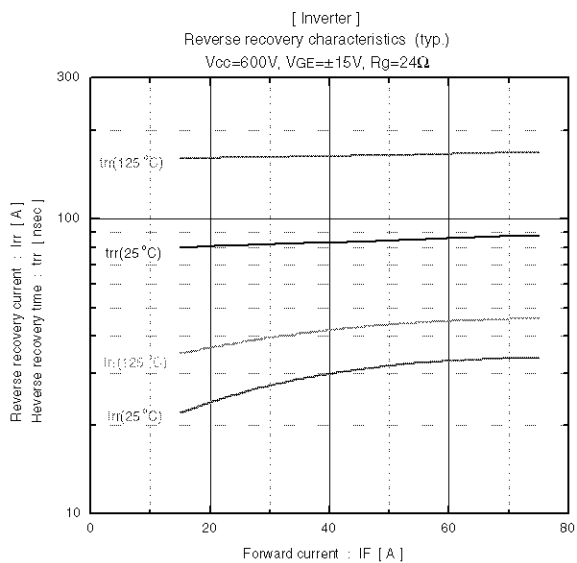
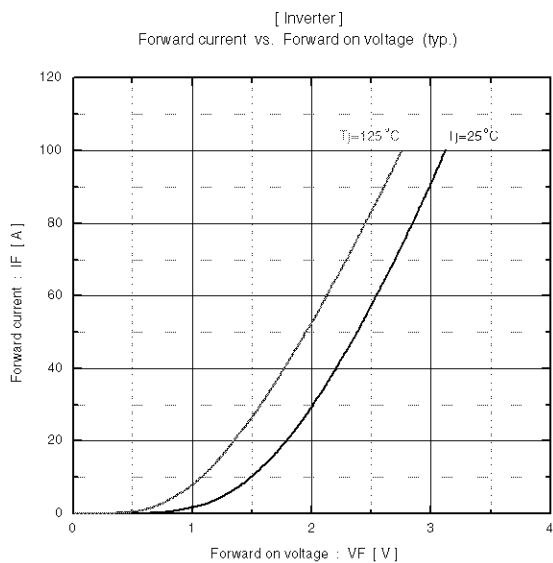
■ Equivalent Circuit Schematic

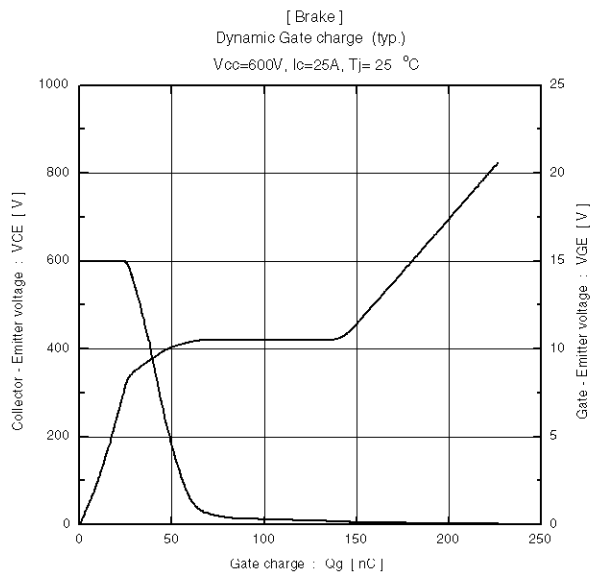
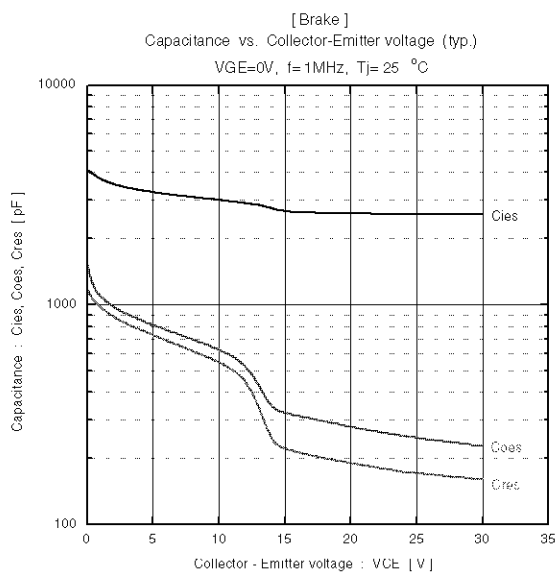
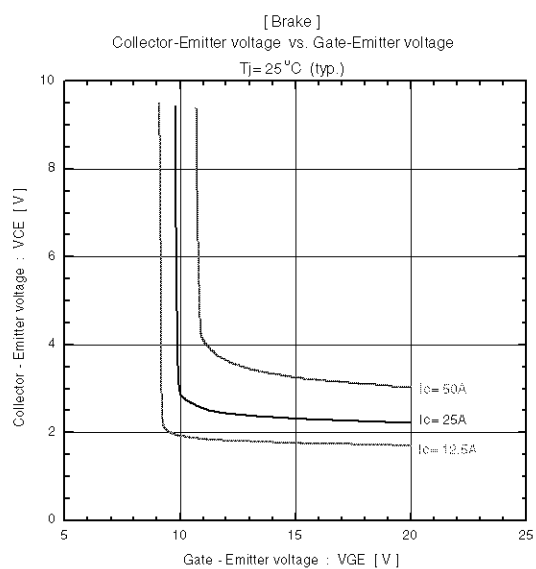
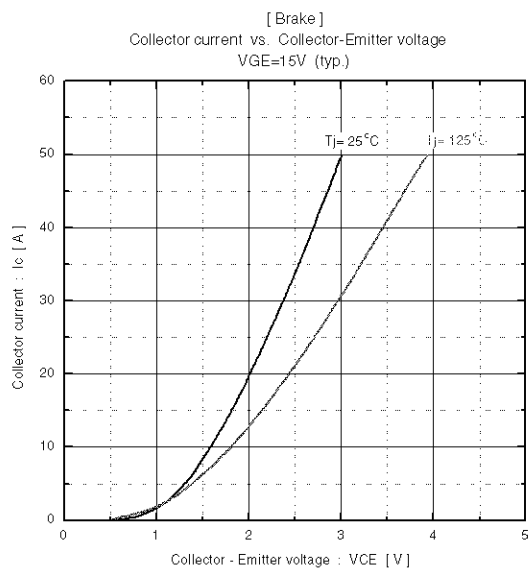
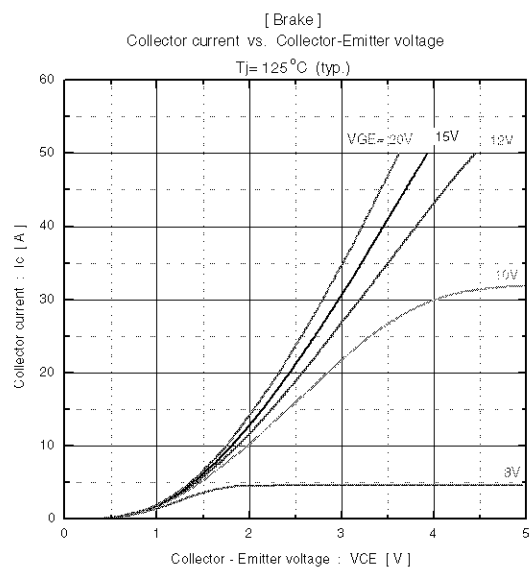
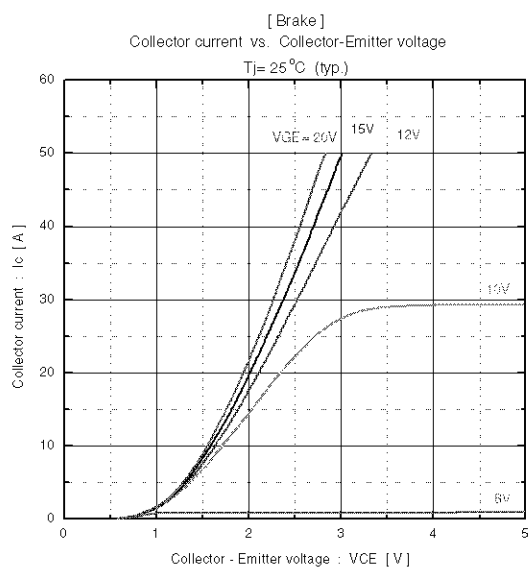


■ Characteristics (Representative)











☐ Shows theory dimensions